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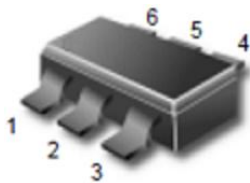
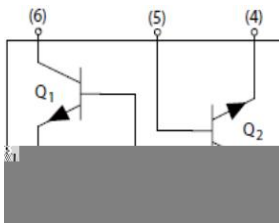


SOT-363 塑封封装双 NPN 半导体三极管。

Double silicon NPN transistor in a SOT-363 Plastic Package.

低电压，低电流。无卤产品。

Low current, Low voltage。HF Product.



PIN 1、 4 : Emitter

PIN 2、 5 : Base

PIN 3、 6 : Collector

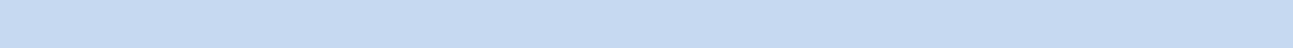
See Marking Instructions.



Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	200	mA
Collector Power Dissipation	P_C	200	mW
	* P_C	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 150	°C

*When mounted on a 7x5x0.6mm ceramic board

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=10\mu A$ $I_E=0$	60			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	40			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\mu A$ $I_C=0$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=30V$ $I_E=0$			0.05	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=3.0V$ $I_C=0$			0.05	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=10mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=1.0V$ $I_C=100mA$	30			
	$h_{FE(3)}$	$V_{CE}=1.0V$ $I_C=50mA$	60			
	$h_{FE(4)}$	$V_{CE}=1.0V$ $I_C=1.0mA$	70			
	$h_{FE(5)}$	$V_{CE}=1.0V$ $I_C=0.1mA$ Bas	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=10mA$ $I_B=1.0mA$			0.2	V
	$V_{CE(sat)(2)}$	$I_C=50mA$ $I_B=5.0mA$			0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=10mA$ $I_B=1.0mA$	0.65		0.85	V



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Note:

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Product Type Code

Lot No. Code, code change with Lot No.



Re

Profile for IR Reflow Soldering(Pb-Free)

- 1 60 90sec;
- 2 5±0.5sec;
- 3 10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
- 3. Cooling Speed: 2~10°C/sec.

260

10±1 sec.

Temp.:260±5°C

Time:10±1 sec

EEL

Package Type
封装形式

Units 包装数量

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